

DME20102

Silicon PNP epitaxial planar type (Tr1)
 Silicon NPN epitaxial planar type (Tr2)

For general amplification

■ Features

- High forward current transfer ratio h_{FE} with excellent linearity
- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

■ Basic Part Number

DSA2002 + DSC2002 (Common emitter)

■ Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

	Parameter	Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	V_{CBO}	-60	V
	Collector-emitter voltage (Base open)	V_{CEO}	-50	V
	Emitter-base voltage (Collector open)	V_{EBO}	-5	V
	Collector current	I_C	-500	mA
	Peak collector current	I_{CP}	-1	A
Tr2	Collector-base voltage (Emitter open)	V_{CBO}	60	V
	Collector-emitter voltage (Base open)	V_{CEO}	50	V
	Emitter-base voltage (Collector open)	V_{EBO}	5	V
	Collector current	I_C	500	mA
	Peak collector current	I_{CP}	1	A
Overall	Total power dissipation	P_T	300	mW
	Junction temperature	T_j	150	$^\circ\text{C}$
	Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Package

- Code

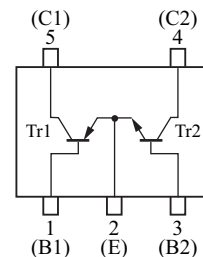
Mini5-G3-B

- Pin Name

- 1: Base (Tr1) 4: Collector (Tr2)
- 2: Emitter (Common) 5: Collector (Tr1)
- 3: Base (Tr2)

■ Marking Symbol: B4

■ Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

• Tr1

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -10 \mu\text{A}, I_E = 0$	-60			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -2 \text{ mA}, I_B = 0$	-50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu\text{A}, I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -20 \text{ V}, I_E = 0$			-0.1	μA
Forward current transfer ratio	h_{FE1}	$V_{CE} = -10 \text{ V}, I_C = -150 \text{ mA}$	120		340	—
	h_{FE2}	$V_{CE} = -10 \text{ V}, I_C = -500 \text{ mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -300 \text{ mA}, I_B = -30 \text{ mA}$		-0.2	-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -300 \text{ mA}, I_B = -30 \text{ mA}$		-0.9	-1.5	V
Transition frequency	f_T	$V_{CE} = -10 \text{ V}, I_C = -50 \text{ mA}$		130		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		7.3	15	pF

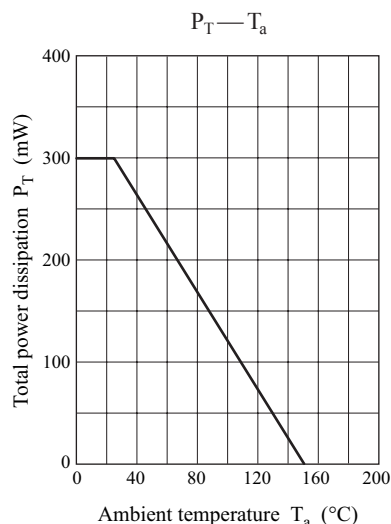
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

• Tr2

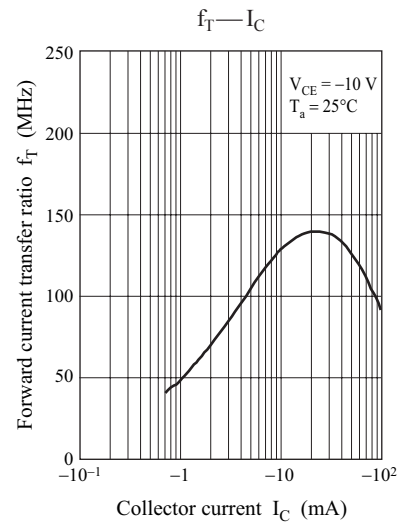
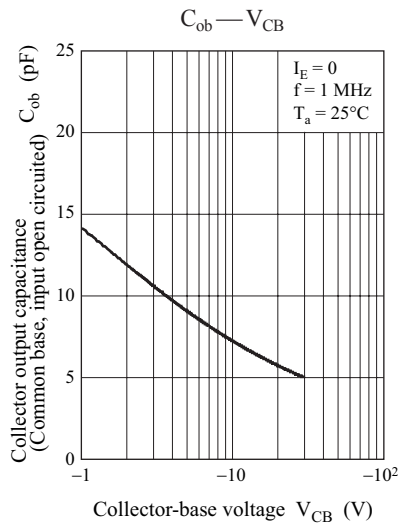
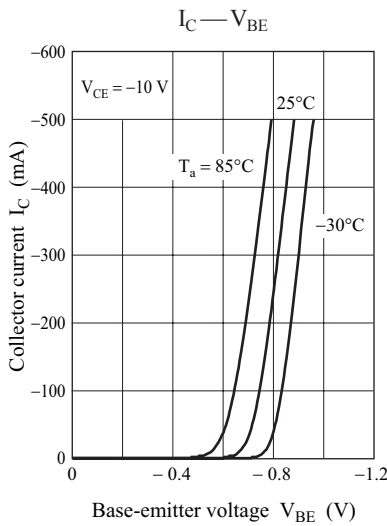
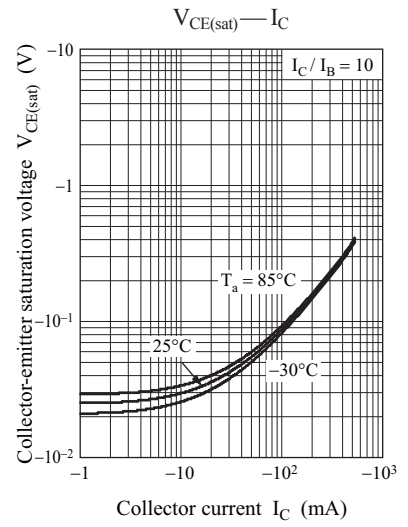
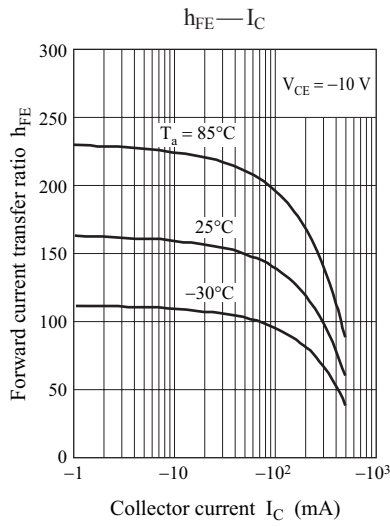
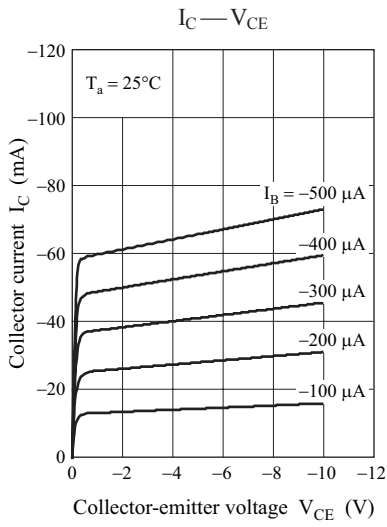
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 10 \mu\text{A}, I_E = 0$	60			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 2 \text{ mA}, I_B = 0$	50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu\text{A}, I_C = 0$	5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 20 \text{ V}, I_E = 0$			0.1	μA
Forward current transfer ratio	h_{FE1}	$V_{CE} = 10 \text{ V}, I_C = 150 \text{ mA}$	120		340	—
	h_{FE2}	$V_{CE} = 10 \text{ V}, I_C = 500 \text{ mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 300 \text{ mA}, I_B = 30 \text{ mA}$		0.1	0.6	V
Transition frequency	f_T	$V_{CE} = 10 \text{ V}, I_C = 50 \text{ mA}$		160		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		4.8	15	pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

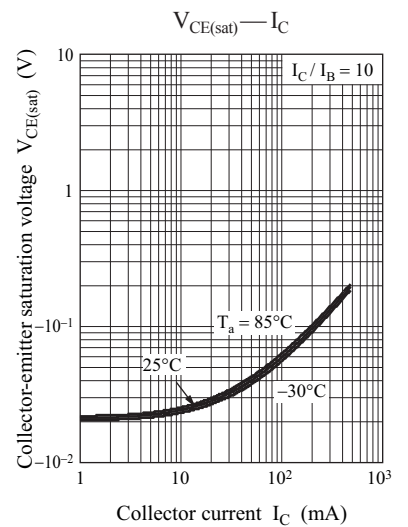
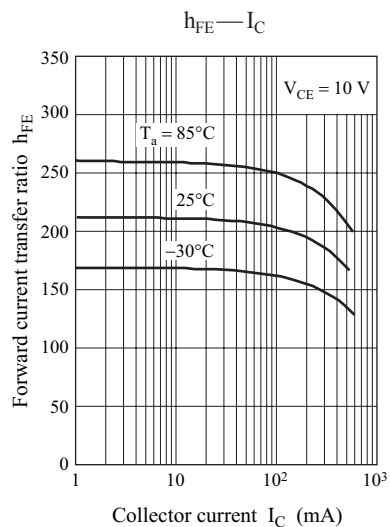
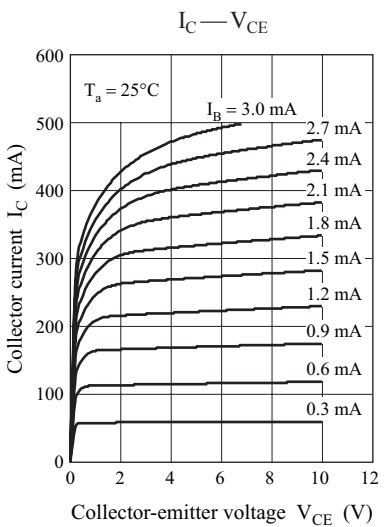
Common characteristics chart

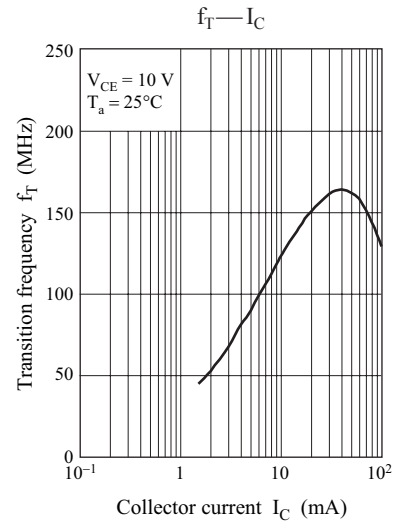
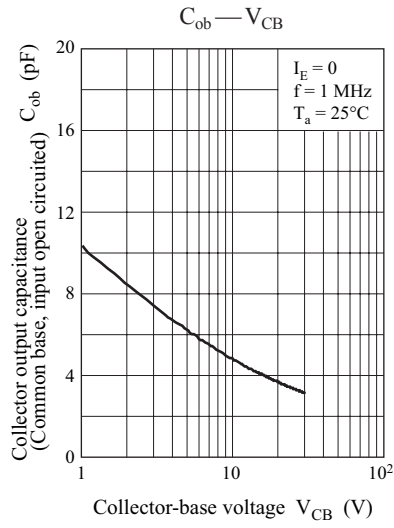
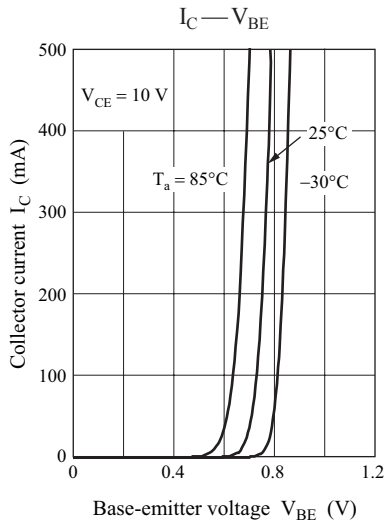


Characteristics charts of Tr1



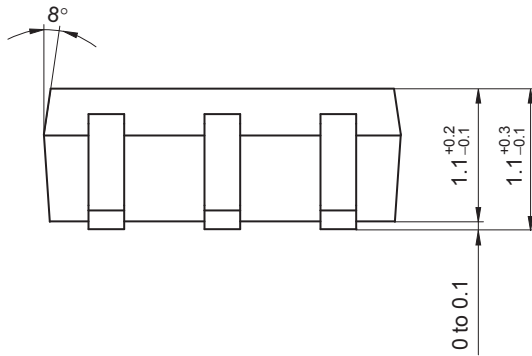
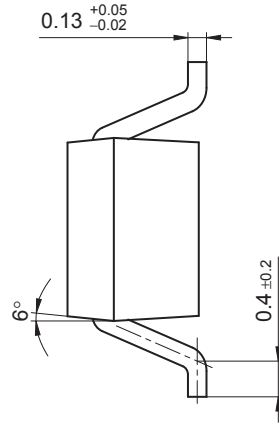
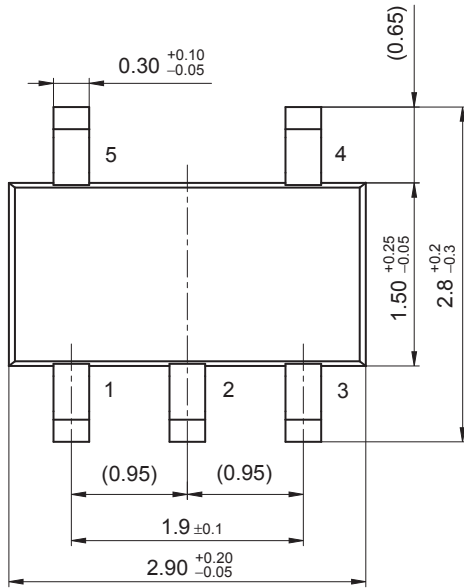
Characteristics charts of Tr2





Mini5-G3-B

Unit: mm



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